

Appl. No. 10/627,849  
Amdt. dated 04/20/05  
Reply to Office Action of 12/21/2004

Attorney Docket No.: N1085-00151  
TSMC2003-0025

**Amendments to the Abstract:**

Please amend the Abstract as indicated in the replacement Abstract which appears on the next page.

### ABSTRACT

A semiconductor device ~~and the method for making same is disclosed.~~ The semiconductor device ~~has~~ includes a substrate and a gate region on top of the a substrate. ~~It further has a first~~ First and second gate sidewall liners are situated on [[a]] first and second sides of the gate region respectively, the first and second sidewall liners having a vertical part contacting sidewalls of the gate region and a horizontal part contacting the substrate, ~~and a first~~ First and second recessed spacers are situated on top of the first and second sidewall liners respectively, ~~wherein a~~ The height of the first and second spacers is lower than [[a]] the height of the gate sidewall liner ~~and~~ wherein whereas the width of the horizontal part of the sidewall liner is shorter than the width of the spacer.